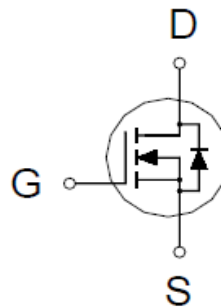
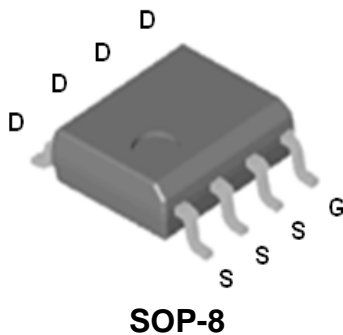


# P4506BV

## N-Channel Logic Level Enhancement Mode MOSFET

### PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	$I_D$
60V	45mΩ @ $V_{GS} = 10V$	5.5A



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS	SYMBOL	LIMITS	UNITS
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	$T_A = 25\text{ }^\circ\text{C}$	5.5
		$T_A = 70\text{ }^\circ\text{C}$	4.5
Pulsed Drain Current <sup>1</sup>	$I_{DM}$	30	A
Avalanche Current	$I_{AS}$	23	
Avalanche Energy	$E_{AS}$	26	mJ
Power Dissipation	$P_D$	$T_A = 25\text{ }^\circ\text{C}$	2.5
		$T_A = 70\text{ }^\circ\text{C}$	1.6
Operating Junction & Storage Temperature Range	$T_j, T_{stg}$	-55 to 150	$^\circ\text{C}$

### THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		25	$^\circ\text{C} / \text{W}$
Junction-to-Ambient	$R_{\theta JA}$		50	

<sup>1</sup>Pulse width limited by maximum junction temperature.

## P4506BV

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#### ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25 °C, Unless Otherwise Noted)

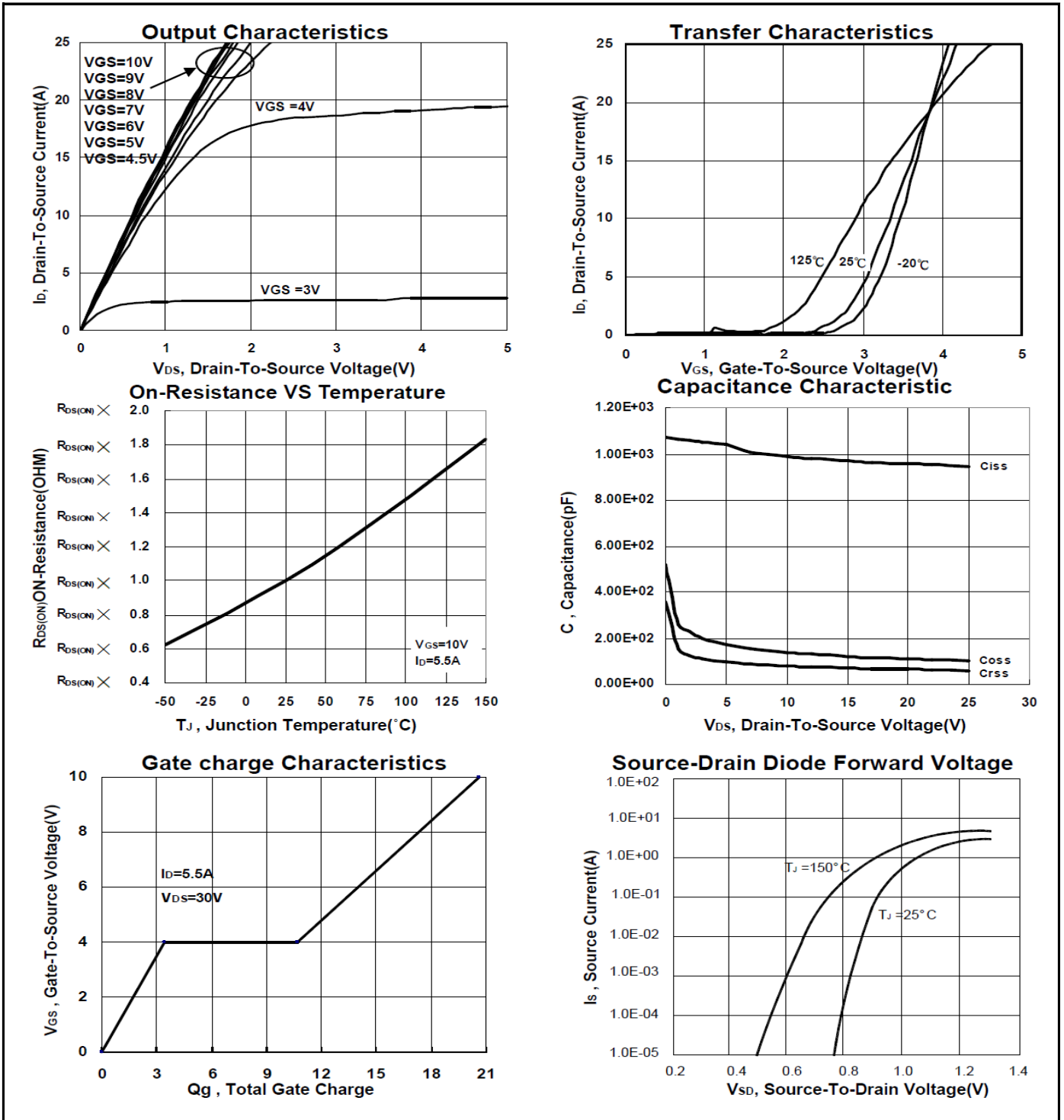
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
<b>STATIC</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	60			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1	1.5	3	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V			1	μA
		V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V, T <sub>C</sub> = 125 °C			10	
On-State Drain Current <sup>1</sup>	I <sub>D(ON)</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 10V	30			A
Drain-Source On-State Resistance <sup>1</sup>	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4.5A		46	65	mΩ
		V <sub>GS</sub> = 10V, I <sub>D</sub> = 5.5A		40	45	
Forward Transconductance <sup>1</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 5.5A		16		S
<b>DYNAMIC</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V, f = 1MHz		969		pF
Output Capacitance	C <sub>oss</sub>			103		
Reverse Transfer Capacitance	C <sub>rss</sub>			62		
Gate Resistance	R <sub>g</sub>	V <sub>GS</sub> = 0V, f = 1MHz		1.6		Ω
Total Gate Charge <sup>2</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 0.5V <sub>(BR)DSS</sub> , V <sub>GS</sub> = 10V, I <sub>D</sub> = 5.5A		21		nC
Gate-Source Charge <sup>2</sup>	Q <sub>gs</sub>			3.6		
Gate-Drain Charge <sup>2</sup>	Q <sub>gd</sub>			7.5		
Turn-On Delay Time <sup>2</sup>	t <sub>d(on)</sub>	V <sub>DS</sub> = 30V, I <sub>D</sub> ≅ 5.5A, V <sub>GS</sub> = 10V, R <sub>GEN</sub> = 6Ω		25		nS
Rise Time <sup>2</sup>	t <sub>r</sub>			188		
Turn-Off Delay Time <sup>2</sup>	t <sub>d(off)</sub>			25		
Fall Time <sup>2</sup>	t <sub>f</sub>			75		
<b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T<sub>J</sub> = 25 °C)</b>						
Continuous Current	I <sub>S</sub>				5.5	A
Forward Voltage <sup>1</sup>	V <sub>SD</sub>	I <sub>F</sub> = 5.5A, V <sub>GS</sub> = 0V			1.3	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 5.5A, dI <sub>F</sub> /dt = 100A/μS		29.5		nS
Reverse Recovery Charge	Q <sub>rr</sub>				25	

<sup>1</sup>Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

<sup>2</sup>Independent of operating temperature.

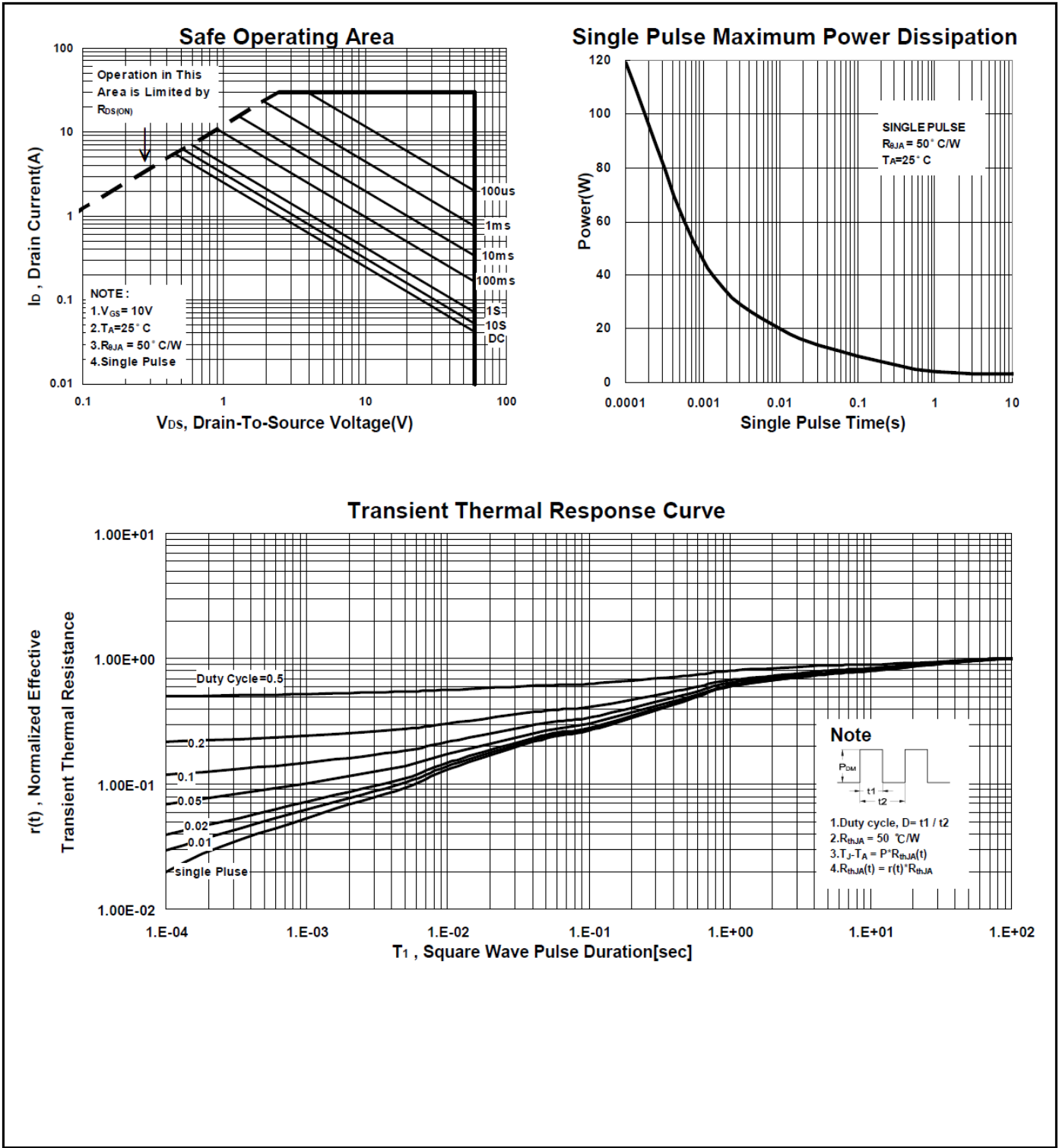
# P4506BV

## N-Channel Logic Level Enhancement Mode MOSFET



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### Package Dimension

### SOP-8 MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8	4.9	5.0	H	0.4	0.6	0.93
B	3.8	3.9	4.0	I	0.19	0.21	0.25
C	5.79	6.0	6.2	J	0.25	0.375	0.5
D	0.33	0.4	0.51	K	0°	3°	18°
E	1.25	1.27	1.29				
F	1.1	1.3	1.65				
G	0.05	0.15	0.25				

